FILM FORMING METHOD

ABSTRACT

A film formation method increases a surface coating rate of a gate insulative film while suppressing deterioration in the electrical characteristics of the gate insulative film. The method includes supplying a vacuum chamber (11) with a gas mixture containing an organic silane compound and an oxidation gas, generating a pulsed high frequency power to intermittently supply a high frequency power, and forming the silicon insulative film on a substrate (S) by plasmatizing the gas mixture with the pulsed high frequency power. The pulsed high frequency power is generated with the largest duty ratio that satisfies a target value of a surface coating rate of the silicon insulative film.

Fig. 1